

N-Channel Enhancement Mode Power MOSFET

■ Features

- Simple Drive Requirement
- Low On-resistance
- Fast Switching

■ Product Summary

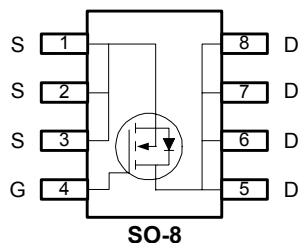
BV_{DSS} (V)	$R_{DS(ON)}$ (m Ω)	I_D (A)
30	6	18

■ General Description

The advanced power MOSFET provides the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The SO-8 package is universally preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

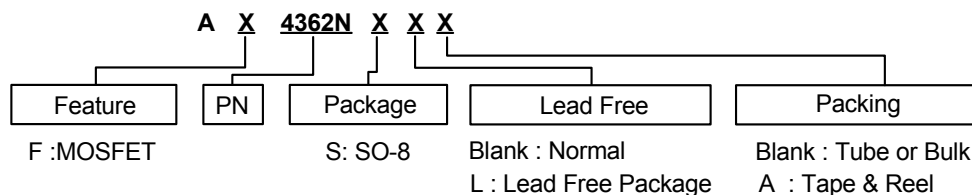
■ Pin Assignments



■ Pin Descriptions

Pin Name	Description
S	Source
G	Gate
D	Drain

■ Ordering information



**AF4362N****N-Channel Enhancement Mode Power MOSFET****■ Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current (Note 1)	$T_A=25^\circ\text{C}$	A
		$T_A=70^\circ\text{C}$	
I_{DM}	Pulsed Drain Current (Note 2)	80	A
P_D	Total Power Dissipation	$T_A=25^\circ\text{C}$	W
	Linear Derating Factor		
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

■ Thermal Data

Symbol	Parameter	Maximum	Units
$R_{thj-amb}$	Thermal Resistance Junction-ambient (Note 1) Max.	50	$^\circ\text{C/W}$

■ Electrical Characteristics at $T_J=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	Reference to 25°C , $I_D=1mA$	-	0.01	-	$V/^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance (Note 3)	$V_{GS}=10V, I_D=18A$	-	-	5	$m\Omega$
		$V_{GS}=4.5V, I_D=12A$	-	-	6	
		$V_{GS}=2.5V, I_D=6A$	-	-	8	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	-	-	1.2	V
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=12A$	-	47	-	S
I_{DSS}	Drain-Source Leakage Current ($T_J=25^\circ\text{C}$)	$V_{DS}=30V, V_{GS}=0V$	-	-	1	μA
	Drain-Source Leakage Current ($T_J=70^\circ\text{C}$)	$V_{DS}=24V, V_{GS}=0V$	-	-	25	
I_{GSS}	Gate-Source Leakage	$V_{GS}=\pm 12V$	-	-	± 100	nA
Q_g	Total Gate Charge (Note 3)	$I_D=18A,$	-	59	95	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=24V,$	-	10	-	
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{GS}=4.5V$	-	23	-	
$t_{d(on)}$	Turn-On Delay Time (Note 3)	$V_{DS}=15V,$	-	16	-	ns
t_r	Rise Time	$I_D=1A,$	-	12	-	
$t_{d(off)}$	Turn-Off Delay Time	$R_G=3.3\Omega, V_{GS}=10V$	-	96	-	
t_f	Fall-Time	$R_D=15\Omega$	-	30	-	
C_{iss}	Input Capacitance	$V_{GS}=0V,$	-	5080	8100	pF
C_{oss}	Output Capacitance	$V_{DS}=25V,$	-	660	-	
C_{rss}	Reverse Transfer Capacitance	$f=1.0MHz$	-	400	-	

■ Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{SD}	Forward On Voltage (Note 3)	$I_S=18A, V_{GS}=0V$	-	-	1.2	V
t_{rr}	Reverse Recovery Time	$I_S=18A, V_{GS}=0V,$	-	43	-	ns
Q_{rr}	Reverse Recovery Charge	$di/dt=100A/\mu s$	-	39	-	nC

Note 1: Surface mounted on 1 in² copper pad of FR4 board; 125 $^\circ\text{C/W}$ when mounted on Min. copper pad.

Note 2: Pulse width limited by Max. junction temperature.

Note 3: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

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■ Typical Performance Characteristics

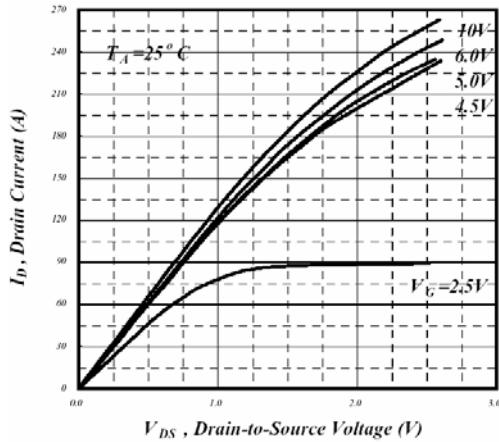


Fig 1. Typical Output Characteristics

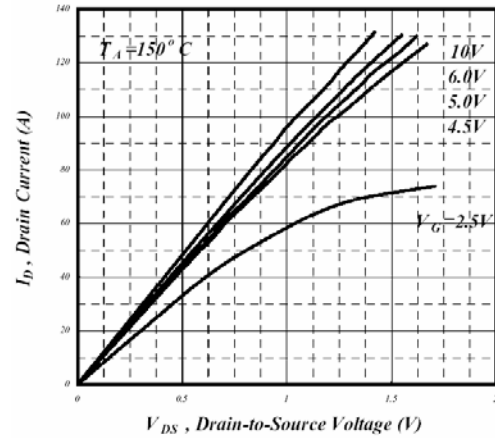


Fig 2. Typical Output Characteristics

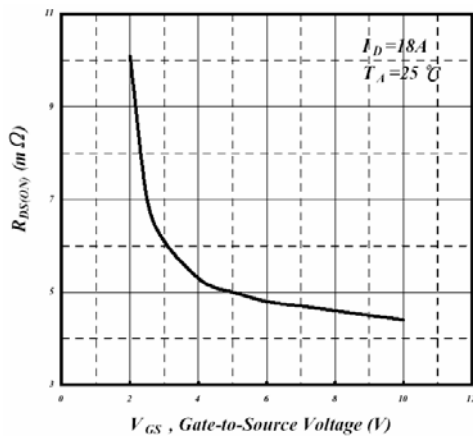


Fig 3. On-Resistance v.s. Gate Voltage

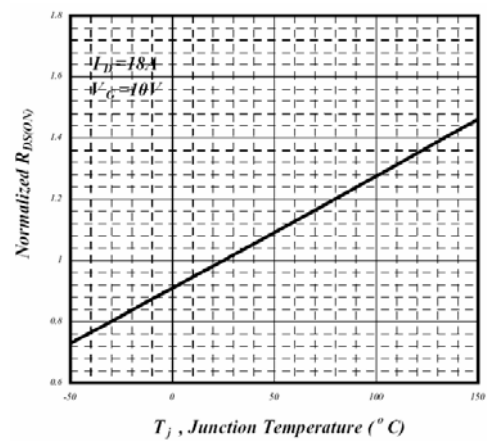


Fig 4. Normalized On-Resistance v.s. Junction Temperature

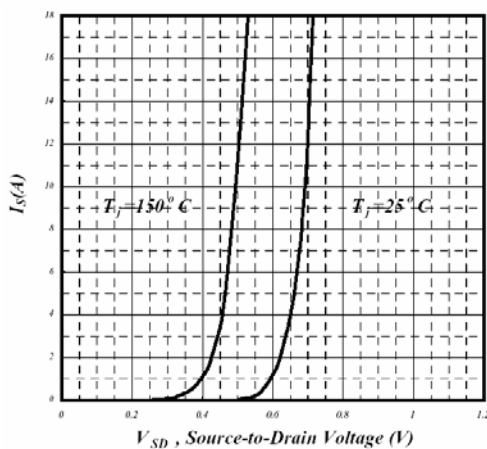


Fig 5. Forward Characteristic of Reverse Diode

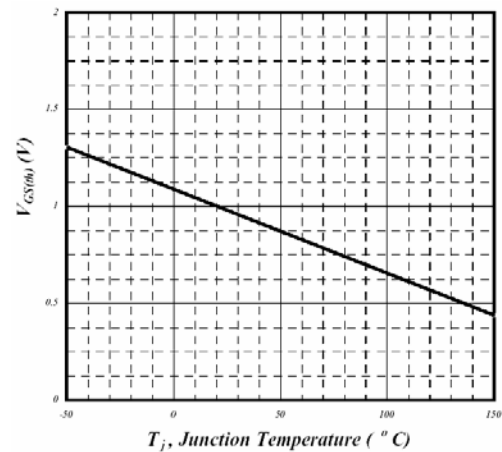


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

■ Typical Performance Characteristics (Continued)

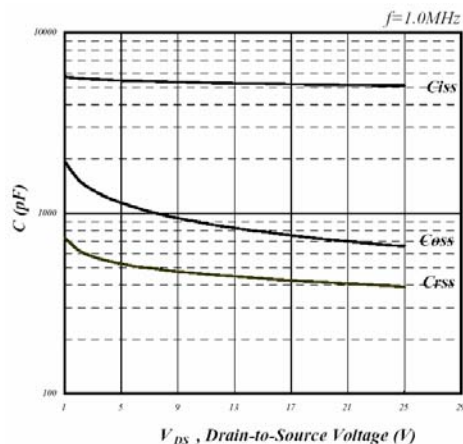


Fig 8. Typical Capacitance Characteristics

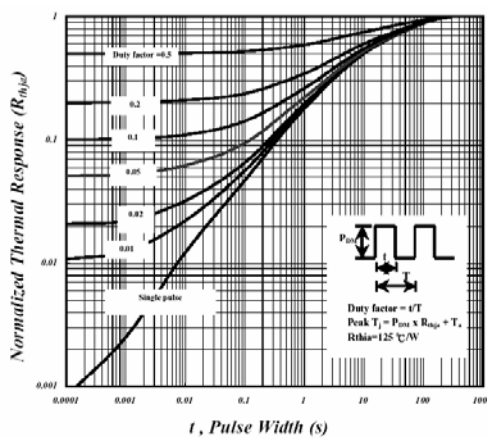


Fig 10. Effective Transient Thermal Impedance

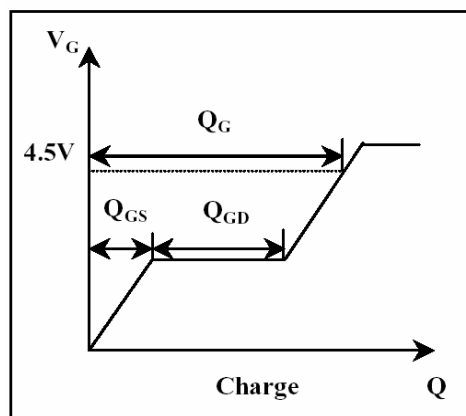
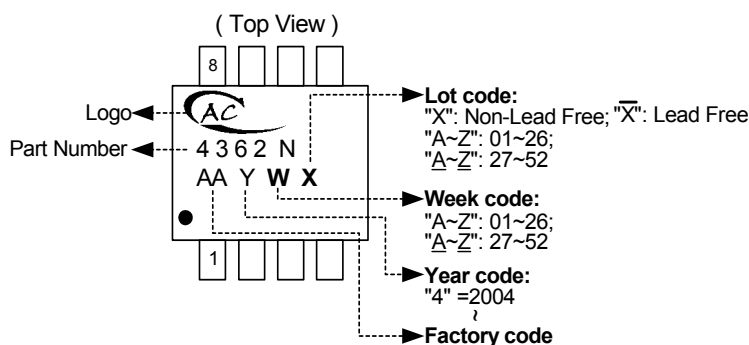


Fig 12. Gate Charge Waveform

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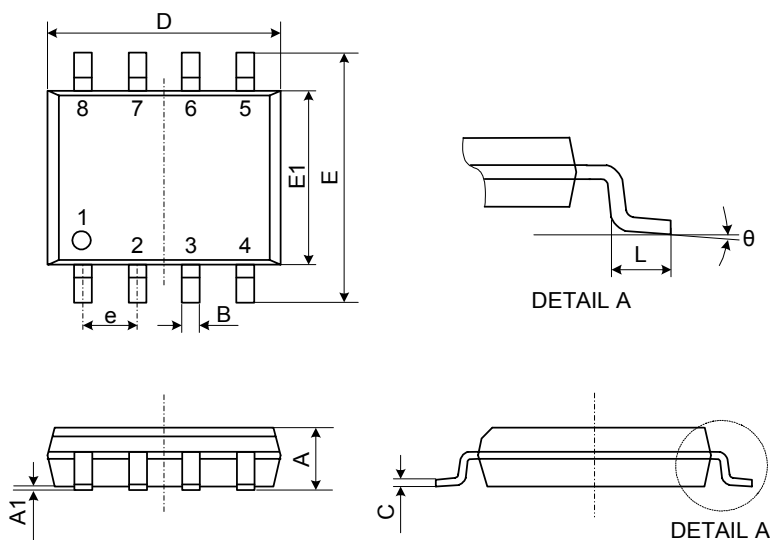
■ Marking Information

SO-8



■ Package Information

Package Type: SO-8



1. All Dimensions Are in Millimeters.
2. Dimension Does Not Include Mold Protrusions.

Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	1.35	1.55	1.75
A1	0.10	0.18	0.25
B	0.33	0.41	0.51
C	0.19	0.22	0.25
D	4.80	4.90	5.00
E	5.80	6.15	6.50
E1	3.80	3.90	4.00
L	0.38	0.71	1.27
θ	0°	4°	8°
e	1.27 TYP.		